

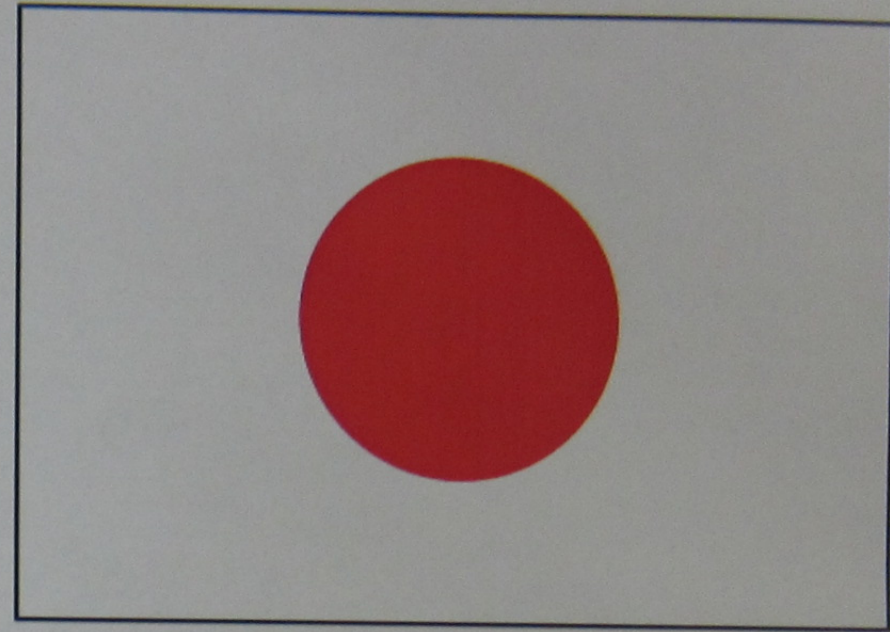
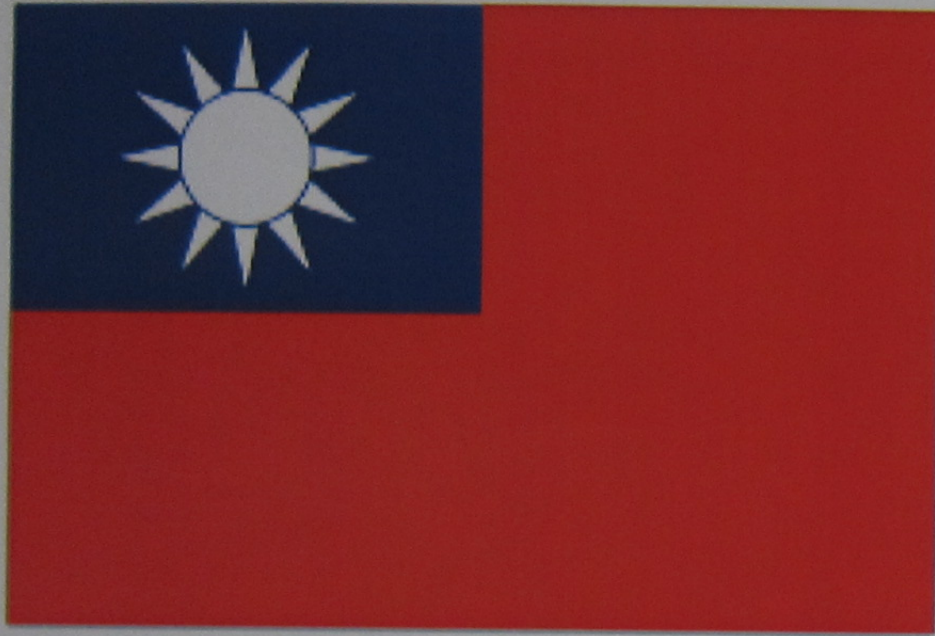
Measurement of Safe Operating Area (SOA)

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Outline

- Introduction to SOA.
- Forward Bias SOA.
 - 1.Measurement.
 - 2.Way to Improve FBSOA of LDMOS.
- Reversed Bias SOA.
 - 1.Unclamped Inductive Switching (UIS) Test Circuit.
 - 2.Clamped Inductive Switching (CIS) Test Circuit.
 - 3.Real Case of UIS and CIS.
- Summary.
- Reference.



Welcome to HANWA

Prof. Ming-Dou Ker (柯明道博士)

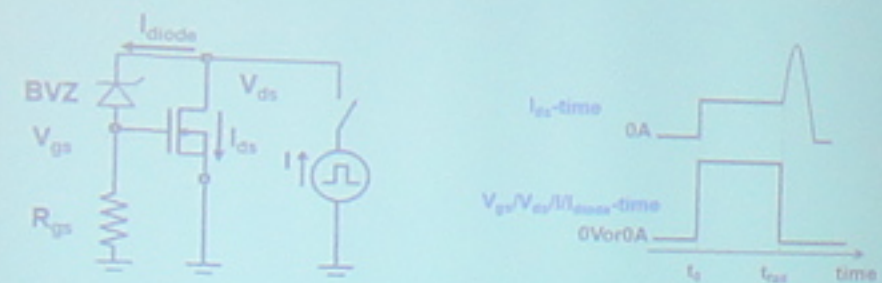
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tSOA Test Circuit and Waveform^[3]

- $t_0 < t_{\text{fall}}$: $V_{\text{gs}} = I_{\text{diode}} \cdot R_{\text{gs}} > V_{\text{th}}$
 $V_{\text{ds}} = I_{\text{diode}} \cdot R_{\text{gs}} + BVZ$
MOS on, $I_{\text{ds}} = I_{\text{MOS, channel}}$
Power dissipation = $V_{\text{ds}} \cdot I_{\text{ds}}$
- $t_{\text{fall}} < t$: Hot carrier turns on parasitic BJT
 $I_{\text{ds}} = I_{\text{BJT}}$, $I_{\text{diode}} = 0A$, $V_{\text{gs}} = V_{\text{ds}} = 0V$, MOS off.



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